

Welcome to **E-XFL.COM**

What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded - Microcontrollers</u>"

Details	
Product Status	Active
Core Processor	RL78
Core Size	16-Bit
Speed	24MHz
Connectivity	CSI, I ² C, LINbus, UART/USART
Peripherals	DMA, LCD, LVD, POR, PWM, WDT
Number of I/O	42
Program Memory Size	16KB (16K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	1K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 9x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LQFP (12x12)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f10wlaafa-50

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

RL78/L13 1. OUTLINE

Pin Count	Package	Data Flash	Fields of	Ordering Part Number
			Application ^{Note}	
64 pins	64-pin plastic LQFP	Mounted	Α	R5F10WLAAFA#30, R5F10WLAAFA#50, R5F10WLCAFA#30,
	(12 × 12 mm, 0.65			R5F10WLCAFA#50, R5F10WLDAFA#30, R5F10WLDAFA#50,
	mm pitch)			R5F10WLEAFA#30, R5F10WLEAFA#50, R5F10WLFAFA#30,
				R5F10WLFAFA#50, R5F10WLGAFA#30, R5F10WLGAFA#50
	64-pin plastic LFQFP	Mounted	Α	R5F10WLAAFB#30, R5F10WLAAFB#50, R5F10WLCAFB#30,
	(10 × 10 mm, 0.5			R5F10WLCAFB#50, R5F10WLDAFB#30, R5F10WLDAFB#50,
	mm pitch)			R5F10WLEAFB#30, R5F10WLEAFB#50, R5F10WLFAFB#30,
				R5F10WLFAFB#50, R5F10WLGAFB#30, R5F10WLGAFB#50,
			G	R5F10WLAGFB#30, R5F10WLAGFB#50, R5F10WLCGFB#30,
				R5F10WLCGFB#50, R5F10WLDGFB#30, R5F10WLDGFB#50,
				R5F10WLEGFB#30, R5F10WLEGFB#50, R5F10WLFGFB#30,
				R5F10WLFGFB#50, R5F10WLGGFB#30, R5F10WLGGFB#50
80 pins	80-pin plastic LQFP	Mounted	Α	R5F10WMAAFA#30, R5F10WMAAFA#50, R5F10WMCAFA#30,
	(14 × 14 mm, 0.65			R5F10WMCAFA#50, R5F10WMDAFA#30, R5F10WMDAFA#50,
	mm pitch)			R5F10WMEAFA#30, R5F10WMEAFA#50, R5F10WMFAFA#30,
				R5F10WMFAFA#50, R5F10WMGAFA#30, R5F10WMGAFA#50
	80-pin plastic LFQFP	Mounted	Α	R5F10WMAAFB#30, R5F10WMAAFB#50, R5F10WMCAFB#30,
	(12 × 12 mm, 0.5			R5F10WMCAFB#50, R5F10WMDAFB#30, R5F10WMDAFB#50,
	mm pitch)			R5F10WMEAFB#30, R5F10WMEAFB#50, R5F10WMFAFB#30,
				R5F10WMFAFB#50, R5F10WMGAFB#30, R5F10WMGAFB#50,
			G	R5F10WMAGFB#30, R5F10WMAGFB#50, R5F10WMCGFB#30,
				R5F10WMCGFB#50, R5F10WMDGFB#30, R5F10WMDGFB#50,
				R5F10WMEGFB#30, R5F10WMEGFB#50, R5F10WMFGFB#30,
				R5F10WMFGFB#50, R5F10WMGGFB#30, R5F10WMGGFB#50

Note For the fields of application, see Figure 1-1 Part Number, Memory Size, and Package of RL78/L13.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.

RL78/L13 1. OUTLINE

1.4 Pin Identification

ANIO, ANI1, PCLBUZ0, PCLBUZ1: Programmable Clock Output/ ANI16 to ANI25: Analog Input **Buzzer Output** AVREFM: Analog Reference Voltage REGC: Regulator Capacitance REMOOUT: Remote control Output Minus AVREFP: RESET: Reset Analog Reference Voltage Plus RTC1HZ: Real-time Clock 2 Correction Clock CAPH, CAPL: Capacitor for LCD (1 Hz) Output COM0 to COM7: LCD Common Output Receive Data RxD0 to RxD3: EXCLK: **External Clock Input** SCK00, SCK10, SCLA0: Serial Clock Input/Output SCL00, SCL10: Serial Clock Output (Main System Clock) **EXCLKS**: **External Clock Input** SDAA0, SDA00, SDA10: Serial Data Input/Output (Subsystem Clock) SEG0 to SEG50: LCD Segment Output SI00, SI10: Serial Data Input INTP0 to INTP7: External Interrupt Input IVCMP0, IVCMP1: Comparator Input SO00, SO10: Serial Data Output IVREF0, IVREF1: Comparator Reference Input TI00 to TI07: Timer Input TO00 to TO07, KR0 to KR7: Key Return P00 to P07: Port 0 TKBO00, TKBO01-0, P10 to P17: Port 1 TKBO01-1, TKBO01-2: Timer Output TOOL0: Data Input/Output for Tool P20 to P27: Port 2 P30 to P35: Port 3 TOOLRxD, TOOLTxD: Data Input/Output for External Device P40 to P47: Port 4 TxD0 to TxD3: Transmit Data P50 to P57: Port 5 VCOUT0, VCOUT1: Comparator Output P60, P61: V_{DD}: Port 6 Power Supply P70 to P77: Port 7 VL1 to VL4: LCD Power Supply P121 to P127: Port 12 Vss: Ground P130, P137: Port 13 X1, X2: Crystal Oscillator (Main System Clock) XT1, XT2: Crystal Oscillator (Subsystem Clock)

RL78/L13 1. OUTLINE

1.6 Outline of Functions

(1/2)

			(112)						
	Item	64-pin	80-pin						
		R5F10WLx (x = A, C-G)	R5F10WMx (x = A, C-G)						
Code flash me	emory (KB)	16 to 128	16 to 128						
Data flash me	emory (KB)	4	4						
RAM (KB)		1 to 8 ^{Note 1} 1 to 8 ^{Note 1}							
Address space	e	1 MB							
Main system clock	High-speed system clock	X1 (crystal/ceramic) oscillation, external main s HS (High-speed main) mode: 1 to 20 MHz (V _{DD} HS (High-speed main) mode: 1 to 16 MHz (V _{DD} = LV (Low-speed main) mode: 1 to 4 MHz (V _{DD} = LV (Low-voltage main) mode: 1 to	= 2.7 to 5.5 V), = 2.4 to 5.5 V), 1.8 to 5.5 V),						
	High-speed on-chip oscillator	HS (High-speed main) mode: 1 to 24 MHz (Vot HS (High-speed main) mode: 1 to 16 MHz (Vot LS (Low-speed main) mode: 1 to 8 MHz (Vot LV (Low-voltage main) mode: 1 to 4 MHz (Vot LV (Low-voltage main) mode: 1 to 4 MHz (Vot LV (Low-voltage main) mode: 1 to 4 MHz (Vot LV (Low-voltage main) mode: 1 to 4 MHz (Vot LV (Low-voltage main) mode: 1 to 4 MHz (Vot LV (Low-voltage main) mode: 1 to 24 MHz (Vot LV (Low-voltage main) mode: 1 to 24 MHz (Vot LV (Low-voltage main) mode: 1 to 24 MHz (Vot LV (Low-voltage main) mode: 1 to 16 MHz (Vot LV (Low-voltage main) mode: 1 to 16 MHz (Vot LV (Low-voltage main) mode: 1 to 16 MHz (Vot LV (Low-voltage main) mode: 1 to 16 MHz (Vot LV (Low-voltage main) mode: 1 to 16 MHz (Vot LV (Low-voltage main) mode: 1 to 16 MHz (Vot LV (LV (LV (LV (LV (LV (LV (LV (LV (LV	o = 2.4 to 5.5 V), = 1.8 to 5.5 V),						
Clock for 16-b	oit timer KB20	48 MHz (TYP.): V _{DD} = 2.7 to 5.5 V							
Subsystem cl	ock	XT1 (crystal) oscillation, external subsystem clo 32.768 kHz (TYP.): V _{DD} = 1.6 to 5.5 V	ock input (EXCLKS)						
Low-speed or	n-chip oscillator	15 kHz (TYP.)							
General-purp	ose register	$(8$ -bit register \times 8) \times 4 banks							
Minimum inst	ruction execution time	0.04167 μ s (High-speed on-chip oscillator: f _H = 24 MHz operation)							
		0.05 μ s (High-speed system clock: f _{MX} = 20 MH	z operation)						
		30.5 μs (Subsystem clock: fsuв = 32.768 kHz op	peration)						
Instruction se	t	 Data transfer (8/16 bits) Adder and subtractor/logical operation (8/16) Multiplication (8 bits × 8 bits) Rotate, barrel shift, and bit manipulation (Set 							
I/O port	Total	49	65						
	CMOS I/O	42 (N-ch O.D. I/O [VDD withstand voltage]: 12)	58 (N-ch O.D. I/O [Vpb withstand voltage]: 18)						
	CMOS input	5	5						
	CMOS output	_	-						
	N-ch O.D I/O (withstand voltage: 6 V)	2	2						
Timer	16-bit timer TAU	8 cha	nnels						
	16-bit timer KB20	1 cha	annel						
	Watchdog timer	1 cha	nnel						
	12-bit interval timer (IT)	1 cha	nnel						
	Real-time clock 2	1 cha	nnel						
	RTC2 output	1 • 1 Hz (subsystem clock: fsub = 32.768 kHz)							
	Timer output	8 channels (PWM outputs: 7 ^{Note 2}) (TAU used) 1 channel (timer KB20 used)							
	Remote control output function	1 (TAU used)							

- **Notes 1.** In the case of the 8 KB, this is about 7 KB when the self-programming function and data flash function are used.
 - 2. The number of outputs varies depending on the setting of the channels in use and the number of master channels (see 6.9.3 Operation as multiple PWM output function in the RL78/L13 User's Manual.).



<R>

2.3 DC Characteristics

2.3.1 Pin characteristics

$(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, high ^{Note 1}	Іон1	Per pin for P00 to P07, P10 to P17, P22 to P27, P30 to P35, P40 to P47, P50 to P57, P70 to P77, P125 to P127, P130	$1.6~V \leq V_{DD} \leq 5.5~V$			-10.0 ^{Note 2}	mA
		Total of P00 to P07, P10 to P17,	$4.0~V \leq V_{DD} \leq 5.5~V$			-90.0	mA
	P22 to P27, P30 to P35, P40 to P47, P50 to P57, P70 to P77, P125 to P127, P130	$2.7 \text{ V} \le V_{DD} \le 4.0 \text{ V}$			-15.0	mA	
		$1.8 \text{ V} \le \text{V}_{DD} \le 2.7 \text{ V}$			-7.0	mA	
		(When duty = 70% ^{Note 3})	$1.6 \text{ V} \le \text{V}_{DD} \le 1.8 \text{ V}$			-3.0	mA
	І он2	Per pin for P20 and P21	$1.6~V \leq V_{DD} \leq 5.5~V$			-0.1 ^{Note 2}	mA
		Total of all pins (When duty = 70% ^{Note 3})	$1.6~V \leq V_{DD} \leq 5.5~V$			-0.2	mA

- **Notes 1**. Value of the current at which the device operation is guaranteed even if the current flows from the V_{DD} pin to an output pin
 - 2. Do not exceed the total current value.
 - 3. Output current value under conditions where the duty factor $\leq 70\%$.

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

- Total output current of pins = (IoH × 0.7)/(n × 0.01)
- <Example> Where n = 80% and I_{OH} = -90.0 mA

Total output current of pins = $(-90.0 \times 0.7)/(80 \times 0.01) \approx -78.75$ mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

Caution P00, P04 to P07, P16, P17, P35, P42 to P44, P46, P47, P53 to P56, and P130 do not output high level in N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.



<R>

$(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, low ^{Note 1}	lo _L 1	Per pin for P00 to P07, P10 to P17, P22 to P27, P30 to P35, P40 to P47, P50 to P57, P70 to P77, P125 to P127, P130				20.0 ^{Note 2}	mA
		Per pin for P60 and P61				15.0 ^{Note 2}	mA
		Total of P40 to P47, P130	$4.0~V \leq V_{DD} \leq 5.5~V$			70.0	mA
		(When duty = 70% ^{Note 3})	$2.7 \text{ V} \le V_{DD} \le 4.0 \text{ V}$			15.0	mA
			$1.8 \text{ V} \le \text{V}_{DD} \le 2.7 \text{ V}$			9.0	mA
			$1.6 \text{ V} \le \text{V}_{DD} < 1.8 \text{ V}$			4.5	mA
		Total of P00 to P07, P10 to P17,	$4.0~V \leq V_{DD} \leq 5.5~V$			90.0	mA
		P22 to P27,	$2.7 \text{ V} \le V_{DD} \le 4.0 \text{ V}$			35.0	mA
		P30 to P35, P50 to P57, P70 to P77, P125 to P127	$1.8 \text{ V} \le \text{V}_{DD} \le 2.7 \text{ V}$			20.0	mA
		(When duty = 70% ^{Note 3})	$1.6 \text{ V} \le \text{V}_{DD} < 1.8 \text{ V}$			10.0	mA
		Total of all pins (When duty = 70% ^{Note 3})				160.0	mA
	l _{OL2}	Per pin for P20 and P21				0.4 ^{Note 2}	mA
		Total of all pins (When duty = 70% ^{Note 3})	$1.6~V \le V_{DD} \le 5.5~V$			0.8	mA

- **Notes 1**. Value of the current at which the device operation is guaranteed even if the current flows from an output pin to the Vss pin
 - 2. Do not exceed the total current value.
 - 3. Output current value under conditions where the duty factor $\leq 70\%$.

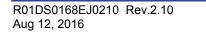
The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

- Total output current of pins = (IoL × 0.7)/(n × 0.01)
 - <Example> Where n = 80% and IoL = 70.0 mA

Total output current of pins = $(70.0 \times 0.7)/(80 \times 0.01) \approx 61.25 \text{ mA}$

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.





$(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol		Conditio		MIN.	TYP.	MAX.	Unit	
Low-speed on- chip oscillator operating current	_{FIL} Note 1								μΑ
RTC2 operating current	I _{RTC} Notes 1, 2, 3	f _{SUB} = 32.768 kHz					0.02		μΑ
12-bit interval timer operating current	I _{TMKA} Notes 1, 2,								μΑ
Watchdog timer operating current	_{WDT} Notes 1, 2, 5	f∟ = 15 kHz	∟ = 15 kHz				0.22		μΑ
A/D converter operating current	ADC Notes 1, 6	When conversion at maximum speed	Normal mode				1.3 0.5	1.7 0.7	mA mA
A/D converter reference voltage current	ADREFNote 1		Low voltage mode, AV _{REFP} = V _{DD} = 3.0 V				75.0		μΑ
Temperature sensor operating current	TMPS Note 1						75.0		μА
LVD operating current	_{LVD} Notes 1, 7						0.08		μΑ
Comparator	ICMPNotes 1, 11	V _{DD} = 5.0 V,	Window mode	Э			12.5		μΑ
operating current		Regulator output	Comparator h	igh-speed m	ode		6.5		μΑ
		voltage = 2.1 V	Comparator lo	ow-speed mo	de		1.7		μΑ
		V _{DD} = 5.0 V,	Window mode	Э			8.0		μΑ
		Regulator output	Comparator h	igh-speed m	ode		4.0		μΑ
		voltage = 1.8 V	Comparator lo	ow-speed mo	de		1.3		μΑ
Self- programming operating current	FSP ^{Notes 1, 9}						2.00	12.20	mA
BGO operating current	BGO ^{Notes 1, 8}						2.00	12.20	mA
SNOOZE	ISNOZ ^{Note 1}	ADC operation	While the mod	de is shifting ^N	lote 10		0.50	0.60	mA
operating current			During A/D co		•		1.20	1.44	mA
		CSI/UART operation	1				0.70	0.84	mA
LCD operating current		External resistance division method	fLCD = fSUB LCD clock = 128 Hz	1/3 bias, four time slices	V _{DD} = 5.0 V, V _{L4} = 5.0 V		0.04	0.20	μΑ
	I _{LCD2} Note 1, 12	Internal voltage boosting method	fLCD = fSUB LCD clock = 128 Hz	1/3 bias, four time slices	$V_{DD} = 3.0 \text{ V},$ $V_{L4} = 3.0 \text{ V}$ $(V_{LCD} = 04\text{H})$		0.85	2.20	μΑ
					$V_{DD} = 5.0 \text{ V},$ $V_{L4} = 5.1 \text{ V}$ $(V_{LCD} = 12\text{H})$		1.55	3.70	μΑ
	I _{LCD3} Note 1, 12	Capacitor split method	fLCD = fSUB LCD clock = 128 Hz	1/3 bias, four time slices	V _{DD} = 3.0 V, V _{L4} = 3.0 V		0.20	0.50	μА

(Notes and Remarks are listed on the next page.)

(5) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (2/2)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol		Conditions	` •	h-speed Mode	`	v-speed Mode	LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Transfer rate		Trans mission	$4.0 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_{b} \le 4.0 \text{ V}$		Note 1		Note 1		Note 1	bps
			Theoretical value of the maximum transfer rate $(C_b = 50 \text{ pF}, R_b = 1.4 \text{ k}\Omega, V_b = 2.7 \text{ V})$		2.8 ^{Note 2}		2.8 ^{Note 2}		2.8 ^{Note 2}	Mbps
			2.7 V ≤ V _{DD} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V		Note 3		Note 3		Note 3	bps
			Theoretical value of the maximum transfer rate $(C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega, V_b = 2.3 \text{ V})$		1.2 ^{Note 4}		1.2 ^{Note 4}		1.2 ^{Note 4}	Mbps
					Notes 5, 6		Notes 5, 6		Notes 5, 6	bps
			Theoretical value of the maximum transfer rate $(C_b = 50 \text{ pF}, R_b = 5.5 \text{ k}\Omega, V_b = 1.6 \text{ V})$		0.43 ^{Note 7}		0.43 ^{Note 7}		0.43 ^{Note 7}	Mbps

Notes 1. The smaller maximum transfer rate derived by using fmck/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 4.0 V \leq V_{DD} \leq 5.5 V and 2.7 V \leq V_b \leq 4.0 V

Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{2.2}{V_b})\} \times 3}$$
 [bps]

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln{(1 - \frac{2.2}{V_b})}\}}{\frac{1}{(\text{Transfer rate})} \times \text{Number of transferred bits}} \times 100 \, [\%]$$

- * This value is the theoretical value of the relative difference between the transmission and reception sides.
- 2. This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to **Note 1** above to calculate the maximum transfer rate under conditions of the customer.
- 3. The smaller maximum transfer rate derived by using fmck/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 2.7 V \leq VDD < 4.0 V and 2.3 V \leq Vb \leq 2.7 V

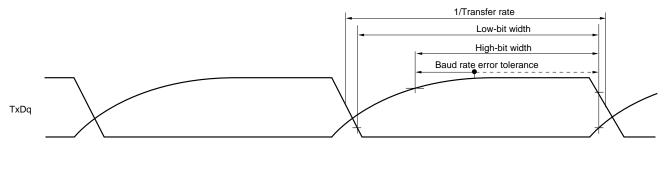
Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{2.0}{V_b})\} \times 3}$$
 [bps]

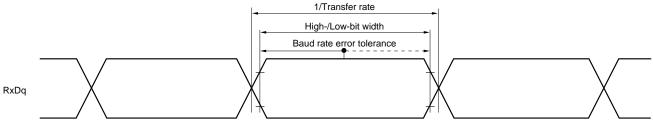
Baud rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln (1 - \frac{2.0}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \, [\%]$$

- * This value is the theoretical value of the relative difference between the transmission and reception sides.
- **4.** This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to **Note 3** above to calculate the maximum transfer rate under conditions of the customer.
- 5. Use it with $V_{DD} \ge V_b$.



UART mode bit width (during communication at different potential) (reference)





- Remarks 1. $R_b[\Omega]$: Communication line (TxDq) pull-up resistance, $C_b[F]$: Communication line (TxDq) load capacitance, $V_b[V]$: Communication line voltage
 - 2. q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 3)
 - 3. fMCK: Serial array unit operation clock frequency(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))

(6) Communication at different potential (2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output, corresponding CSI00 only)

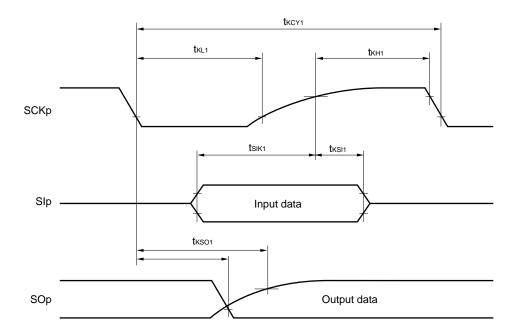
 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol		Conditions	HS (high	h-speed Mode	,	/-speed Mode	,	-voltage Mode	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	tксү1	tkcy1 ≥ 2/fcLk	$ 4.0 \ V \leq V_{DD} \leq 5.5 \ V, $ $ 2.7 \ V \leq V_b \leq 4.0 \ V, $ $ C_b = 20 \ pF, \ R_b = 1.4 \ k\Omega $	200		1150		1150		ns
			$ 2.7 \text{ V} \leq \text{V}_{DD} < 4.0 \text{ V}, \\ 2.3 \text{ V} \leq \text{V}_{b} \leq 2.7 \text{ V}, \\ C_{b} = 20 \text{ pF}, R_{b} = 2.7 \text{ k}\Omega $	300		1150		1150		ns
SCKp high-level width	t кн1	$4.0 \text{ V} \le \text{V}_{DD} \le 5$ $C_b = 20 \text{ pF}, R_b = 100 \text{ pF}$.5 V, 2.7 V \leq V _b \leq 4.0 V, = 1.4 kΩ	tkcy1/2 – 50		tксү1/2 — 50		txcy1/2 - 50		ns
		$2.7 \text{ V} \le \text{V}_{DD} < 4.$ $C_b = 20 \text{ pF}, R_b = 1.$	0 V, 2.3 V \leq V _b \leq 2.7 V, = 2.7 kΩ	tkcy1/2 - 120		tксү1/2 — 120		tkcy1/2 - 120		ns
SCKp low-level width	t KL1	$4.0 \text{ V} \le \text{V}_{DD} \le 5$ $C_b = 20 \text{ pF}, R_b = 100 \text{ pF}$.5 V, 2.7 V \leq V _b \leq 4.0 V, = 1.4 kΩ	tkcy1/2 –		tксү1/2 — 50		tксү1/2 — 50		ns
		$2.7 \text{ V} \le \text{V}_{DD} < 4.$ $C_b = 20 \text{ pF}, R_b = 1.$	0 V, 2.3 V \leq V _b \leq 2.7 V, = 2.7 kΩ	tkcy1/2 –		tксү1/2 — 50		tксү1/2 — 50		ns
SIp setup time (to SCKp↑) ^{Note 1}	tsıĸı	$4.0 \text{ V} \le \text{V}_{DD} \le 5$ $C_b = 20 \text{ pF}, R_b = 100 \text{ pF}$.5 V, 2.7 V \leq V _b \leq 4.0 V, = 1.4 kΩ	58		479		479		ns
		$2.7 \text{ V} \le \text{V}_{DD} < 4.$ $C_b = 20 \text{ pF}, R_b = 1.$	0 V, 2.3 V \leq V _b \leq 2.7 V, = 2.7 kΩ	121		479		479		ns
SIp hold time (from SCKp↑) ^{Note}	tksi1	$4.0 \text{ V} \le \text{V}_{DD} \le 5$ $C_b = 20 \text{ pF}, R_b = 100 \text{ pF}$.5 V, 2.7 V \leq V _b \leq 4.0 V, = 1.4 kΩ	10		10		10		ns
1		$2.7 \text{ V} \le \text{V}_{DD} < 4.$ $C_b = 20 \text{ pF}, R_b = 1.$	0 V, 2.3 V \leq V _b \leq 2.7 V, = 2.7 kΩ	10		10		10		ns
Delay time from SCKp↓ to	tkso1	$4.0 \text{ V} \le \text{V}_{DD} \le 5$ $C_b = 20 \text{ pF}, R_b = 100 \text{ pF}$.5 V, 2.7 V \leq V _b \leq 4.0 V, = 1.4 kΩ		60		60		60	ns
SOp output ^{Note 1}		$2.7 \text{ V} \le \text{V}_{DD} < 4.$ $C_b = 20 \text{ pF}, R_b = 1.$	0 V, 2.3 V \leq V _b \leq 2.7 V, = 2.7 kΩ		130		130		130	ns
SIp setup time (to SCKp↓) ^{Note 2}	tsıĸ1	$4.0 \text{ V} \le \text{V}_{DD} \le 5$ $C_b = 20 \text{ pF}, R_b = 100 \text{ pF}$.5 V, 2.7 V \leq V _b \leq 4.0 V, = 1.4 kΩ	23		110		110		ns
		$2.7 \text{ V} \le \text{V}_{DD} < 4.$ $C_b = 20 \text{ pF}, R_b = 1.$	0 V, 2.3 V \leq V _b \leq 2.7 V, = 2.7 kΩ	33		110		110		ns
SIp hold time (from SCKp↓) ^{Note}	t KSI1	$4.0 \text{ V} \le \text{V}_{DD} \le 5$ $C_b = 20 \text{ pF}, R_b = 100 \text{ pF}$.5 V, 2.7 V \leq V _b \leq 4.0 V, = 1.4 kΩ	10		10		10		ns
2		2.7 V ≤ V _{DD} < 4. C _b = 20 pF, R _b	0 V, 2.3 V \leq V _b \leq 2.7 V, = 2.7 kΩ	10		10		10		ns
Delay time from SCKp↑ to	tkso1	$4.0 \text{ V} \le \text{V}_{DD} \le 5$ $C_b = 20 \text{ pF}, R_b = 100 \text{ pF}$.5 V, 2.7 V \leq V _b \leq 4.0 V, = 1.4 kΩ		10		10		10	ns
SOp output ^{Note 2}		2.7 V ≤ V _{DD} < 4. C _b = 20 pF, R _b	0 V, 2.3 V \leq V _b \leq 2.7 V, = 2.7 kΩ		10		10		10	ns

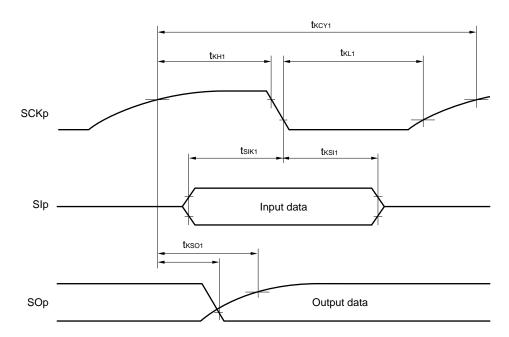
(Notes, Caution and Remarks are listed on the next page.)



CSI mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remarks 1. R_b[Ω]: Communication line (SCKp, SOp) pull-up resistance, C_b[F]: Communication line (SCKp, SOp) load capacitance, V_b[V]: Communication line voltage

- 2. p: CSI number (p = 00, 10), m: Unit number, n: Channel number (mn = 00, 02), g: PIM and POM number (g = 0, 1)
- fmck: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00)

(9) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I^2C mode) (1/2) (T_A = -40 to +85°C, 1.8 V \leq V_{DD} \leq 5.5 V, Vss = 0 V)

Parameter	Symbol	Conditions		h-speed Mode		v-speed Mode	,	v-voltage) Mode	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLr clock frequency	fscL	$\begin{aligned} 4.0 & \ V \leq V_{DD} \leq 5.5 \ V, \\ 2.7 & \ V \leq V_b \leq 4.0 \ V, \\ C_b & = 50 \ pF, \ R_b = 2.7 \ k\Omega \end{aligned}$		1000 ^{Note}		300 ^{Note 1}		300 ^{Note 1}	kHz
		$\begin{split} 2.7 & \ V \le V_{DD} < 4.0 \ V, \\ 2.3 & \ V \le V_b \le 2.7 \ V, \\ C_b & = 50 \ pF, \ R_b = 2.7 \ k\Omega \end{split}$		1000 ^{Note}		300 ^{Note 1}		300 ^{Note 1}	kHz
		$\begin{aligned} 4.0 & \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}, \\ 2.7 & \text{ V} \leq \text{V}_{\text{b}} \leq 4.0 \text{ V}, \\ \text{C}_{\text{b}} &= 100 \text{ pF}, \text{ R}_{\text{b}} = 2.8 \text{ k}\Omega \end{aligned}$		400 ^{Note 1}		300 ^{Note 1}		300 ^{Note 1}	kHz
		$ 2.7 \text{ V} \le \text{V}_{DD} < 4.0 \text{ V}, \\ 2.3 \text{ V} \le \text{V}_{b} \le 2.7 \text{ V}, \\ C_{b} = 100 \text{ pF}, R_{b} = 2.7 \text{ k}\Omega $		400 ^{Note 1}		300 ^{Note 1}		300 ^{Note 1}	kHz
		$\begin{aligned} &1.8 \text{ V } (2.4 \text{ V}^{\text{Note 2}}) \leq \text{V}_{\text{DD}} < 3.3 \text{ V}, \\ &1.6 \text{ V} \leq \text{V}_{\text{b}} \leq 2.0 \text{ V}^{\text{Note 3}}, \\ &\text{C}_{\text{b}} = 100 \text{ pF}, \text{ R}_{\text{b}} = 5.5 \text{ k}\Omega \end{aligned}$		300 ^{Note 1}		300 ^{Note 1}		300 ^{Note 1}	kHz
Hold time when SCLr = "L"	tLOW	$\begin{aligned} 4.0 & \ V \le V_{DD} \le 5.5 \ V, \\ 2.7 & \ V \le V_b \le 4.0 \ V, \\ C_b & = 50 \ pF, \ R_b = 2.7 \ k\Omega \end{aligned}$	475		1550		1550		ns
		$\begin{split} 2.7 & \ V \le V_{DD} < 4.0 \ V, \\ 2.3 & \ V \le V_b \le 2.7 \ V, \\ C_b & = 50 \ pF, \ R_b = 2.7 \ k\Omega \end{split}$	475		1550		1550		ns
		$\begin{aligned} 4.0 & \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}, \\ 2.7 & \text{ V} \leq \text{V}_{\text{b}} \leq 4.0 \text{ V}, \\ \text{C}_{\text{b}} &= 100 \text{ pF}, \text{ R}_{\text{b}} = 2.8 \text{ k}\Omega \end{aligned}$	1150		1550		1550		ns
		$\begin{split} 2.7 & \text{ V} \leq \text{V}_{\text{DD}} < 4.0 \text{ V}, \\ 2.3 & \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V}, \\ \text{C}_{\text{b}} = 100 \text{ pF}, \text{ R}_{\text{b}} = 2.7 \text{ k}\Omega \end{split}$	1150		1550		1550		ns
		$ \begin{aligned} &1.8 \text{ V } (2.4 \text{ V}^{\text{Note 2}}) \leq \text{V}_{\text{DD}} < 3.3 \text{ V}, \\ &1.6 \text{ V} \leq \text{V}_{\text{b}} \leq 2.0 \text{ V}^{\text{Note 3}}, \\ &C_{\text{b}} = 100 \text{ pF}, \text{ R}_{\text{b}} = 5.5 \text{ k}\Omega \end{aligned} $	1550		1550		1550		ns
Hold time when SCLr = "H"	thigh	$\begin{aligned} 4.0 & \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}, \\ 2.7 & \text{ V} \leq \text{V}_{\text{b}} \leq 4.0 \text{ V}, \\ C_{\text{b}} & = 50 \text{ pF}, R_{\text{b}} = 2.7 \text{ k}\Omega \end{aligned}$	245		610		610		ns
		$2.7 \text{ V} \le \text{V}_{DD} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{b} \le 2.7 \text{ V},$ $C_{b} = 50 \text{ pF}, R_{b} = 2.7 \text{ k}\Omega$	200		610		610		ns
		$ 4.0 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}, \\ 2.7 \text{ V} \leq \text{V}_{b} \leq 4.0 \text{ V}, \\ C_{b} = 100 \text{ pF}, R_{b} = 2.8 \text{ k}\Omega $	675		610		610		ns
		$2.7 \text{ V} \le \text{V}_{DD} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{b} \le 2.7 \text{ V},$ $C_{b} = 100 \text{ pF}, R_{b} = 2.7 \text{ k}\Omega$	600		610		610		ns
		$\begin{split} 1.8 \ V \ & (2.4 \ V^{Note \ 2}) \leq V_{DD} < 3.3 \ V, \\ 1.6 \ V \leq V_{b} \leq 2.0 \ V^{Note \ 3}, \\ C_{b} = 100 \ pF, \ R_{b} = 5.5 \ k \Omega \end{split}$	610		610		610		ns

(Notes and Caution are listed on the next page, and Remarks are listed on the page after the next page.)



(1) I²C standard mode (2/2)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	` `	h-speed Mode	`	LS (low-speed main) Mode		LV (low-voltage main) Mode	
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Data setup time	tsu:dat	2.7 V ≤ V _{DD} ≤ 5.5 V	250		250		250		ns
(reception)		$1.8 \text{ V } (2.4 \text{ V}^{\text{Note 3}}) \le \text{V}_{\text{DD}} \le 5.5 \text{ V}$	250		250		250		ns
		1.6 V ≤ V _{DD} ≤ 5.5 V	-	_	_	_	250		ns
Data hold time	thd:dat	2.7 V ≤ V _{DD} ≤ 5.5 V	0	3.45	0	3.45	0	3.45	μs
(transmission)Note 2		$1.8 \text{ V } (2.4 \text{ V}^{\text{Note 3}}) \le \text{V}_{\text{DD}} \le 5.5 \text{ V}$	0	3.45	0	3.45	0	3.45	μs
		1.6 V ≤ V _{DD} ≤ 5.5 V	-	_	_	_	0	3.45	μs
Setup time of stop	tsu:sto	$2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}$	4.0		4.0		4.0		μs
condition		$1.8 \text{ V } (2.4 \text{ V}^{\text{Note 3}}) \le \text{V}_{\text{DD}} \le 5.5 \text{ V}$	4.0		4.0		4.0		μs
		1.6 V ≤ V _{DD} ≤ 5.5 V	1	_	_	_	4.0		μs
Bus-free time	t BUF	$2.7~\text{V} \leq \text{V}_{\text{DD}} \leq 5.5~\text{V}$	4.7		4.7		4.7		μs
		$1.8 \text{ V } (2.4 \text{ V}^{\text{Note 3}}) \le \text{V}_{\text{DD}} \le 5.5 \text{ V}$	4.7		4.7		4.7		μs
		1.6 V ≤ V _{DD} ≤ 5.5 V	1	_	_	_	4.7		μs

Notes 1. The first clock pulse is generated after this period when the start/restart condition is detected.

- 2. The maximum value (MAX.) of thd:DAT is during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.
- 3. Condition in HS (high-speed main) mode

Caution The values in the above table are applied even when bit 2 (PIOR2) in the peripheral I/O redirection register (PIOR) is 1. At this time, the pin characteristics (IOH1, IOL1, VOH1, VOL1) must satisfy the values in the redirect destination.

Remark The maximum value of C_b (communication line capacitance) and the value of R_b (communication line pull-up resistor) at that time in each mode are as follows.

Standard mode: C_b = 400 pF, R_b = 2.7 k Ω

LVD Detection Voltage of Interrupt & Reset Mode

(Ta = -40 to +85°C, VPDR \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol		Cond	ditions	MIN.	TYP.	MAX.	Unit
Interrupt and reset	VLVD13	VPOC2,	V _{POC1} , V _{POC0} = 0, 0, 0,	falling reset voltage	1.60	1.63	1.66	V
mode	VLVD12		LVIS1, LVIS0 = 1, 0 Rising release reset v		1.74	1.77	1.81	V
				Falling interrupt voltage	1.70	1.73	1.77	V
	VLVD11		LVIS1, LVIS0 = 0, 1	Rising release reset voltage	1.84	1.88	1.91	V
				Falling interrupt voltage	1.80	1.84	1.87	V
	V _{LVD4}		LVIS1, LVIS0 = 0, 0	Rising release reset voltage	2.86	2.92	2.97	V
				Falling interrupt voltage	2.80	2.86	2.91	V
	VLVD11	VPOC2,	V _{POC1} , V _{POC0} = 0, 0, 1,	falling reset voltage	1.80	1.84	1.87	V
	VLVD10		LVIS1, LVIS0 = 1, 0	Rising release reset voltage	1.94	1.98	2.02	V
				Falling interrupt voltage	1.90	1.94	1.98	V
	V _L VD9		LVIS1, LVIS0 = 0, 1	Rising release reset voltage	2.05	2.09	2.13	V
			Falling interrupt voltage	2.00	2.04	2.08	V	
	VLVD2	LVIS1, LVIS0 = 0, 0	Rising release reset voltage	3.07	3.13	3.19	V	
			Falling interrupt voltage	3.00	3.06	3.12	V	
	V _{LVD8}	VPOC2,	V _{POC1} , V _{POC0} = 0, 1, 0,	falling reset voltage	2.40	2.45	2.50	V
	V _{LVD7}		LVIS1, LVIS0 = 1, 0	Rising release reset voltage	2.56	2.61	2.66	V
			LVIS1, LVIS0 = 0, 1	Falling interrupt voltage	2.50	2.55	2.60	V
	V _{LVD6}			Rising release reset voltage	2.66	2.71	2.76	V
				Falling interrupt voltage	2.60	2.65	2.70	V
	V _{LVD1}		LVIS1, LVIS0 = 0, 0	Rising release reset voltage	3.68	3.75	3.82	V
				Falling interrupt voltage	3.60	3.67	3.74	V
	V _{LVD5}	VPOC2,	V _{POC1} , V _{POC0} = 0, 1, 1,	falling reset voltage	2.70	2.75	2.81	V
	V _{LVD4}		LVIS1, LVIS0 = 1, 0	Rising release reset voltage	2.86	2.92	2.97	V
				Falling interrupt voltage	2.80	2.86	2.91	V
	V _{LVD3}		LVIS1, LVIS0 = 0, 1	Rising release reset voltage	2.96	3.02	3.08	V
				Falling interrupt voltage	2.90	2.96	3.02	V
	V _{LVD0}		LVIS1, LVIS0 = 0, 0	Rising release reset voltage	3.98	4.06	4.14	V
				Falling interrupt voltage	3.90	3.98	4.06	V

2.6.6 Supply voltage rising slope characteristics

$(T_A = -40 \text{ to } +85^{\circ}\text{C}, \text{ Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
V _{DD} rising slope	SVDD				54	V/ms

Caution Make sure to keep the internal reset state by the LVD circuit or an external reset until V_{DD} reaches the operating voltage range shown in 2.4 AC Characteristics.

2.7 LCD Characteristics

2.7.1 External resistance division method

(1) Static display mode

(TA = -40 to +85°C, VL4 (MIN.) \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
LCD drive voltage	V _{L4}		2.0		V _{DD}	V

(2) 1/2 bias method, 1/4 bias method

(TA = -40 to +85°C, VL4 (MIN.) \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
LCD drive voltage	V _{L4}		2.7		V _{DD}	V

(3) 1/3 bias method

(T_A = -40 to +85°C, V_{L4} (MIN.) \leq V_{DD} \leq 5.5 V, Vss = 0 V)

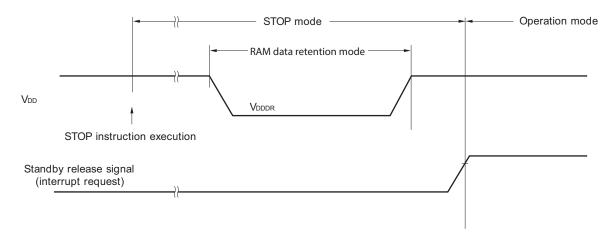
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
LCD drive voltage	V _{L4}		2.5		V _{DD}	V

<R> 2.8 RAM Data Retention Characteristics

$(T_A = -40 \text{ to } +85^{\circ}\text{C})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage	VDDDR		1.46 ^{Note}		5.5	V

- <R> Note This depends on the POR detection voltage. For a falling voltage, data in RAM are retained until the voltage reaches the level that triggers a POR reset but not once it reaches the level at which a POR reset is generated.
- <R> Caution Data in RAM are not retained if the CPU operates outside the specified operating voltage range.
 Therefore, place the CPU in STOP mode before the operating voltage drops below the specified range.



2.9 Flash Memory Programming Characteristics

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
System clock frequency	fclk	1.8 V ≤ V _{DD} ≤ 5.5 V	1		24	MHz
Number of code flash rewrites ^{Notes 1, 2, 3}	Cerwr	Retained for 20 years TA = 85°C	1,000			Times
Number of data flash rewrites ^{Notes 1, 2, 3}		Retained for 1 year T _A = 25°C		1,000,000		
		Retained for 5 years TA = 85°C	100,000			
		Retained for 20 years T _A = 85°C	10,000			

- Notes 1. 1 erase + 1 write after the erase is regarded as 1 rewrite. The retaining years are until next rewrite after the
 - 2. When using flash memory programmer and Renesas Electronics self programming library
 - 3. This characteristic indicates the flash memory characteristic and based on Renesas Electronics reliability test.

Remark When updating data multiple times, use the flash memory as one for updating data.

2.10 Dedicated Flash Memory Programmer Communication (UART)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate		During serial programming	115,200		1,000,000	bps

3.1 Absolute Maximum Ratings

Absolute Maximum Ratings (1/3)

Parameter	Symbol	Conditions	Ratings	Unit
Supply voltage	V _{DD}		-0.5 to +6.5	V
REGC pin input voltage	Virego	REGC	-0.3 to +2.8 and -0.3 to V _{DD} +0.3 ^{Note 1}	V
Input voltage	V _{I1}	P00 to P07, P10 to P17, P20 to P27, P30 to P35, P40 to P47, P50 to P57, P60, P61, P70 to P77, P121 to P127, P130, P137	-0.3 to V _{DD} +0.3 ^{Note 2}	V
	V ₁₂	P60 and P61 (N-ch open-drain) EXCLK, EXCLKS, RESET	-0.3 to +6.5 -0.3 to V _{DD} +0.3 ^{Note 2}	V
Output voltage	Vo1	P00 to P07, P10 to P17, P20 to P27, P30 to P35, P40 to P47, P50 to P57, P60, P61, P70 to P77, P121 to P127, P130, P137	-0.3 to V _{DD} +0.3 ^{Note 2}	V
Analog input voltage	Val1	ANI0, ANI1, ANI16 to ANI26	-0.3 to V _{DD} +0.3 and -0.3 to AV _{REF(+)} +0.3 ^{Notes 2, 3}	V

- **Notes 1.** Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F). This value regulates the absolute maximum rating of the REGC pin. Do not use this pin with voltage applied to it.
 - 2. Must be 6.5 V or lower.
 - 3. Do not exceed $AV_{REF(+)} + 0.3 V$ in case of A/D conversion target pin.
- Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.
- **Remarks 1.** Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.
 - **2.** $AV_{REF (+)}$: + side reference voltage of the A/D converter.
 - 3. Vss: Reference voltage



3.2 Oscillator Characteristics

3.2.1 X1 and XT1 oscillator characteristics

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Resonator	Conditions	MIN.	TYP.	MAX.	Unit
X1 clock oscillation	Ceramic resonator/	$2.7~V \leq V_{DD} \leq 5.5~V$	1.0		20.0	MHz
frequency (fx)Note	crystal resonator	2.4 V ≤ V _{DD} < 2.7 V	1.0		16.0	
XT1 clock oscillation frequency (fxT)Note	Crystal resonator		32	32.768	35	kHz

Note Indicates only permissible oscillator frequency ranges. Refer to **AC Characteristics** for instruction execution time. Request evaluation by the manufacturer of the oscillator circuit mounted on a board to check the oscillator characteristics.

Caution Since the CPU is started by the high-speed on-chip oscillator clock after a reset release, check the X1 clock oscillation stabilization time using the oscillation stabilization time counter status register (OSTC) by the user. Determine the oscillation stabilization time of the OSTC register and the oscillation stabilization time select register (OSTS) after sufficiently evaluating the oscillation stabilization time with the resonator to be used.

Remark When using the X1 oscillator and XT1 oscillator, see **5.4 System Clock Oscillator** in the RL78/L13 User's Manual.

3.2.2 On-chip oscillator characteristics

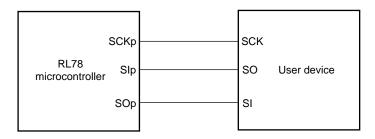
 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions			TYP.	MAX.	Unit
High-speed on-chip oscillator clock frequencyNotes 1, 2	fін			1		24	MHz
High-speed on-chip oscillator		+85 to +105°C	$2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	-2		+2	%
clock frequency accuracy		–20 to +85°C	$2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	-1		+1	%
		-40 to −20°C	$2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	-1.5		+1.5	%
Low-speed on-chip oscillator clock frequency	fıL		•		15		kHz
Low-speed on-chip oscillator clock frequency accuracy				-15		+15	%

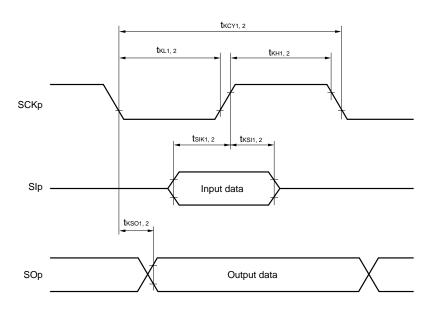
- **Notes 1.** The high-speed on-chip oscillator frequency is selected by bits 0 to 4 of the option byte (000C2H/010C2H) and bits 0 to 2 of the HOCODIV register.
 - 2. This indicates the oscillator characteristics only. Refer to **AC Characteristics** for the instruction execution time.



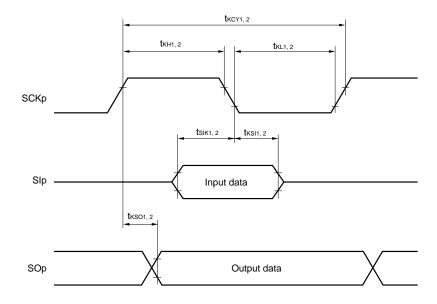
CSI mode connection diagram (during communication at same potential)



CSI mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remarks 1. p: CSI number (p = 00, 10)

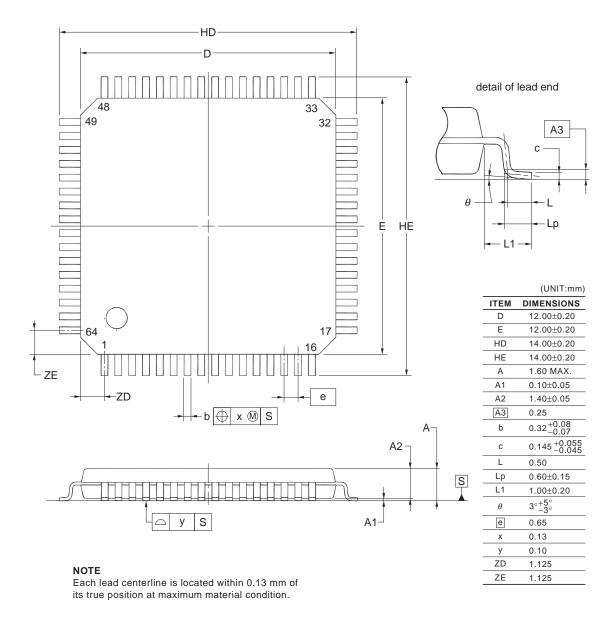
2. m: Unit number, n: Channel number (mn = 00, 02)

4. PACKAGE DRAWINGS

4.1 64-pin Products

R5F10WLAAFA, R5F10WLCAFA, R5F10WLDAFA, R5F10WLEAFA, R5F10WLFAFA, R5F10WLGAFA

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LQFP64-12x12-0.65	PLQP0064JA-A	P64GK-65-UET-2	0.51



©2012 Renesas Electronics Corporation. All rights reserved.

R5F10WMAAFB, R5F10WMCAFB, R5F10WMDAFB, R5F10WMEAFB, R5F10WMFAFB, R5F10WMGAFB, R5F10WMAGFB, R5F10WMCGFB, R5WMCGFB, R5WMCGF

